

Amendments to the Claims

This listing of claims replaces all prior versions, and listings, of claims in the above-identified application:

Listing of Claims

1-50. Cancelled

51. (Original) A planarization method comprising:

positioning a metal-containing surface of a substrate to interface with a polishing surface; wherein the metal-containing surface comprises a metal selected from the group consisting of a Group VIII^B metal, a Group IB metal, and a combination thereof;

supplying a planarization composition in proximity to the interface; and

planarizing the substrate surface;

wherein the planarization composition comprises a halogen-containing compound and a halide salt, with the proviso that the planarization composition does not include abrasive particles.

52. (Original) The method of claim 51 wherein the metal-containing surface of the substrate comprises a metal selected from the group consisting of a Group VIII^B metal, a Group IB metal, and a combination thereof, which is in elemental form or an alloy thereof.

53. (Original) The method of claim 51 wherein the metal-containing surface of the substrate comprises a metal selected from the group consisting of a Group VIII^B second row metal, a Group VIII^B third row metal, a Group IB second row metal, a Group IB third row metal, and a combination thereof.

54. (Original) The method of claim 53 wherein the metal-containing surface of the substrate comprises a metal selected from the group consisting of Rh, Pd, Pt, Ir, and Ru.
55. (Original) The method of claim 54 wherein the metal-containing surface comprises elemental platinum.
56. (Original) The method of claim 51 wherein the metal is present in an amount of about 50 atomic percent or more.
57. (Original) The method of claim 51 wherein the substrate is a semiconductor substrate or substrate assembly.
58. (Original) The method of claim 51 which is carried out in one step.
59. (Original) The method of claim 51 wherein the halogen-containing compound is selected from the group consisting of a halogen, an interhalogen, a halogen-generating compound, and combinations thereof.
60. (Original) The method of claim 51 wherein the halogen-containing compound is selected from the group consisting of a halogen; an interhalogen; a halogen-generating compound selected from the group consisting of XeF₂, HgF₂, SF₄, alkyl halides, and complexes of halogen with organic bases; and combinations thereof.
61. (Original) The method of claim 51 wherein the halogen-containing compound is selected from the group consisting of F₂, Cl₂, Br₂, I₂, ClBr, IBr, ICl, BrF, ClF, ClF₃, BrF₃, ClF₅, IF₅, IF₇, XeF₂, HgF₂, SF₄, alkyl halides, and complexes of halogen with organic bases, and combinations thereof.

62. (Original) The method of claim 51 wherein the halogen-containing compound is selected from the group consisting of ClBr, IBr, ICl, BrF, ClF, ClF₃, BrF₃, ClF₅, IF₅, IF₇, XeF₂, HgF₂, SF₄, alkyl halides, and complexes of halogen with organic bases, and combinations thereof.
63. (Original) The method of claim 51 wherein the halide salt is an inorganic salt.
64. (Original) The method of claim 63 wherein the inorganic halide salt is selected from the group consisting of NaI, KCl, KBr, NH₄F, and combinations thereof.
65. (Original) The method of claim 51 wherein the halide salt is an organic salt.
66. (Original) The method of claim 65 wherein the organic salt is selected from the group consisting of Et₄NBr, Me₃NHCl, Me₄NF, and combinations thereof.
67. (Original) The method of claim 51 wherein the halogen-containing compound is present in the planarization composition in an amount of at least about 0.1% by weight and the halide salt is present in the planarization composition in an amount of at least about 0.1% by weight.
68. (Original) The method of claim 51 wherein the halogen-containing compound is present in the planarization composition in an amount of about 1% to about 10% by weight.
69. (Original) The method of claim 51 wherein the halide salt is present in the planarization composition in an amount of about 1% to about 10% by weight.
70. (Original) The method of claim 51 wherein the halogen of the halogen-containing compound is different than the halogen of the halide salt.

71. **(Original)** The method of claim 51 wherein the planarization composition is not basic.
72. **(Original)** The method of claim 51 wherein the polishing surface comprises a fixed abrasive article.
73. **(Original)** A planarization method comprising:
- providing a semiconductor substrate or substrate assembly including at least one region of a platinum-containing surface;
 - providing a polishing surface;
 - providing a planarization composition at an interface between the at least one region of platinum-containing surface and the polishing surface; and
 - planarizing the at least one region of platinum-containing surface;
- wherein the planarization composition comprises a halogen-containing compound and a halide salt, with the proviso that the planarization composition does not include abrasive particles.
74. **(Original)** The method of claim 73 wherein the platinum-containing surface of the substrate comprises platinum in elemental form.
75. **(Original)** The method of claim 73 wherein the platinum is present in an amount of about 50 atomic percent or more.
76. **(Original)** The method of claim 73 wherein the semiconductor substrate or substrate assembly is a silicon wafer.

77. (Original) The method of claim 73 wherein the halogen-containing compound is selected from the group consisting of a halogen, an interhalogen, a halogen-generating compound, and combinations thereof.
78. (Original) The method of claim 73 wherein the halogen-containing compound is selected from the group consisting of a halogen; an interhalogen; a halogen-generating compound selected from the group consisting of XeF_2 , HgF_2 , SF_4 , alkyl halides, and complexes of halogen with organic bases; and combinations thereof.
79. (Original) The method of claim 73 wherein the halogen-containing compound is selected from the group consisting of F_2 , Cl_2 , Br_2 , I_2 , ClBr , IBr , ICl , BrF , ClF , ClF_3 , BrF_3 , ClF_5 , IF_5 , IF_7 , XeF_2 , HgF_2 , SF_4 , alkyl halides, and complexes of halogen with organic bases, and combinations thereof.
80. (Original) The method of claim 73 wherein the halide salt is an inorganic salt.
81. (Original) The method of claim 80 wherein the inorganic halide salt is selected from the group consisting of NaI , KCl , KBr , NH_4F and combinations thereof.
82. (Original) The method of claim 73 wherein the halide salt is an organic salt.
83. (Original) The method of claim 82 wherein the organic salt is selected from the group consisting of Et_4NBr , Me_3NHCl , Me_4NF , and combinations thereof.
84. (Original) The method of claim 73 wherein the halogen-containing compound is present in the planarization composition in an amount of at least about 0.1% by weight and the halide salt is present in the planarization composition in an amount of at least about 0.1% by weight.

85. (Original) The method of claim 73 wherein the halogen-containing compound is present in the planarization composition in an amount of about 1% to about 10% by weight.

86. (Original) The method of claim 73 wherein the halide salt is present in the planarization composition in an amount of about 1% to about 10% by weight.

87. (Original) The method of claim 73 wherein the polishing surface comprises a fixed abrasive article.

88. (Original) A planarization method for use in forming an interconnect, the method comprising:

providing a semiconductor substrate or substrate assembly having a patterned dielectric layer formed thereon and a metal-containing layer formed over the patterned dielectric layer, wherein the metal-containing layer comprises a metal selected from the group consisting of a Group VIIIB metal, a Group IB metal, and a combination thereof;

positioning a first portion of a polishing surface for contact with the metal-containing layer;

providing a planarization composition in proximity to the contact between the polishing surface and the metal-containing layer; and

planarizing the metal-containing layer;

wherein the planarization composition comprises a halogen-containing compound and a halide salt, with the proviso that the planarization composition does not include abrasive particles.

89. (Original) The method of claim 88 wherein the halogen-containing compound is selected from the group consisting of a halogen, an interhalogen, a halogen-generating compound, and combinations thereof.

90. (Original) The method of claim 88 wherein the halogen-containing compound is selected from the group consisting of a halogen; an interhalogen; a halogen-generating compound selected from the group consisting of XeF_2 , HgF_2 , SF_4 , alkyl halides, and complexes of halogen with organic bases; and combinations thereof.
91. (Original) The method of claim 88 wherein the halogen-containing compound is selected from the group consisting of F_2 , Cl_2 , Br_2 , I_2 , ClBr , IBr , ICl , BrF , ClF , ClF_3 , BrF_3 , ClF_5 , IF_5 , IF_7 , XeF_2 , HgF_2 , SF_4 , alkyl halides, and complexes of halogen with organic bases, and combinations thereof.
92. (Original) The method of claim 88 wherein the halide salt is an inorganic salt.
93. (Original) The method of claim 92 wherein the inorganic halide salt is selected from the group consisting of NaI , KCl , KBr , NH_4F and combinations thereof.
94. (Original) The method of claim 88 wherein the halide salt is an organic salt.
95. (Original) The method of claim 94 wherein the organic salt is selected from the group consisting of Et_4NBr , Me_3NHCl , Me_4NF , and combinations thereof.
96. (Original) The method of claim 88 wherein the halogen-containing compound is present in the planarization composition in an amount of at least about 0.1% by weight.
97. (Original) The method of claim 96 wherein the halogen-containing compound is present in the planarization composition in an amount of about 1% to about 10% by weight.

98. **(Original)** The method of claim 88 wherein the halide salt is present in the planarization composition in an amount of at least about 0.1% by weight.
99. **(Original)** The method of claim 98 wherein the halide salt is present in the planarization composition in an amount of about 1% to about 10% by weight.
100. **(Original)** The method of claim 88 wherein the polishing surface comprises a fixed abrasive article.
101. **(Original)** A planarization method comprising:
- positioning a metal-containing surface of a substrate to interface with a polishing surface comprising a fixed abrasive article, wherein the metal-containing surface comprises a metal selected from the group consisting of a Group VIIIB metal, a Group IB metal, and a combination thereof;
 - supplying a planarization composition in proximity to the interface; and
 - planarizing the substrate surface;
- wherein the planarization composition comprises a halogen-containing compound and a halide salt.
102. **(Original)** A planarization method comprising:
- providing a semiconductor substrate or substrate assembly including at least one region of a platinum-containing surface;
 - providing a polishing surface comprising a fixed abrasive article;
 - providing a planarization composition at an interface between the at least one region of platinum-containing surface and the polishing surface; and
 - planarizing the at least one region of platinum-containing surface;

wherein the planarization composition comprises a halogen-containing compound and a halide salt.

103. **(Original)** A planarization method for use in forming an interconnect, the method comprising:

providing a semiconductor substrate or substrate assembly having a patterned dielectric layer formed thereon and a metal-containing layer formed over the patterned dielectric layer, wherein the metal-containing layer comprises a metal selected from the group consisting of a Group VIIIB metal, a Group IB metal, and a combination thereof;

positioning a first portion of a polishing surface comprising a fixed abrasive article for contact with the metal-containing layer;

providing a planarization composition in proximity to the contact between the polishing surface and the metal-containing layer; and

planarizing the metal-containing layer;

wherein the planarization composition comprises a halogen-containing compound and a halide salt.